

Low Voltage and Low Power Divide-By-2/3 Counter Design Using Pass Transistor Logic Circuit Technique

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Abstract—

An extended true-single-phase-clock (E-TSPC) based divide-by-2/3 counter design for low supply voltage and low power consumption applications is presented. By using a wired OR scheme; only one transistor is needed to implement both the counting logic and the mode selection control. This can enhance the working frequency of the counter due to a reduced critical path between the E-TSPC flip flops (FFs). Since the number of transistor stacking between the power rails is kept at merely two, the proposed design is sustainable to low V_{DD} operations (531 MHz at 0.6 V V_{DD}) for the power saving purpose. Simulation results show that compared with two classic E-TSPC based designs in 0.18 μ m process technology, as much as 16.4% in operation speed and 39% in power-delay-product can be achieved by the proposed design.

Index Terms—

Extended true-single-phase-clock flip flops (E-TSPC FF), low power, low voltage, prescaler.

I. INTRODUCTION

High speed divide-by $N/N + 1$ counter (also called prescaler) is a fundamental module for frequency synthesizers. Its design is crucial because it operates at a higher frequency and consumes higher power consumption. A divide-by- $N/N + 1$ counter consists of flip-flops (FF) and extra logic, which determines the terminal count. Conventional high speed FF based divide-by $N/N + 1$ counter designs use current-mode logic (CML) latches [1] and suffer from the disadvantage of large load capacitance. This not only limits the maximum operating frequency and current-drive capabilities, but also increases the total power consumption. Alternatively, FF based divide-by $N/N + 1$ designs adopt dynamic logic FFs such as true-single-phase clock (TSPC) [2]–[4]. The designs can be further enhanced by using extended true-single-phase-clock (E-TSPC) FFs for high speed and low power Applications [5]–[10]. E-TSPC designs remove the transistor stacked structure so that all the transistors are free of the body effect. They are thus more sustainable for high operating frequency operations in the face of low voltage supply. Past optimization efforts on prescaler designs focused on simplifying the logic part to reduce the circuit complexity and the critical path delay. For example, an E-TSPC design embedded with one extra pMOS/nMOS transistor can form an integrated function of FF and AND/OR logic [7]. Moving part of the control logic to the first FF to

reduce unnecessary FF toggling yields another version of prescaler design [8]. These two classic designs each contains 16 transistors only and the mode control logic uses as few as 4 transistors. To achieve such circuit simplicity, it calls for a ratioed structure in the FF design. Despite its distinct speed performance, the incurred static and short circuit power consumptions are significant. Latest designs presented in [10] adopt a general TSPC logic family containing both ratioed and ratioless inverter alternatives. Since the maximum height of transistor stacking is up to 5, these designs lose their performance advantages when working under a low scenario. In [11], a power gating technique by inserting an extra pMOS between and the FF is employed in two novel divide-by-2/3 counter designs. The unused FF can be shut down when working in the divide-by-2 mode. Due to the increase in the number of transistor stacking (up to 4), these designs are not suitable for low operations. Due to the quadratic dependence of power consumption on supply voltage, lowering is a very effective measure to reduce the power at the expense of speed performance. In this paper, a prescaler circuit design aimed at tackling the speed and power issues simultaneously using non-state-of-the-art process technology (0.18 μm) is presented. In particular, we focus on low operations for power saving without sacrificing the speed performance. In this design, ratioed E-TSPC FFs are employed due to its circuit simplicity and speed performance. Only one pass transistor is needed to implement the mode control logic. The proposed design is capable of working at a maximum frequency of 531 MHz when the supply voltage is as low as 0.6 V.

II. CONVENTIONAL E-TSPC-BASED DIVIDE-BY-2/3

COUNTER DESIGNS

A state-of-the-art divide-by-2/3 counter design is given in Fig. 1(a) [7]. It contains two E-TSPC-based FFs and two logic gates i.e., an OR gate and an AND gate. When the divide control signal DC is “0”, the OR gate (merged into output of FF1 design) is disabled. The state of (Q1b, Q2b) cycles through 11, 01, and 00. This corresponds to a di-verse-by-3 function. Note that state 10 is a forbidden state. If, somehow, the circuit enters this state, the next state will go back to a valid state, 11 automatically. When DC is “1”, the output of FF1 will be disabled and FF2 alone performs the divide-by-2 function. Since the input to FF1 is not disabled, FF1 toggles as usual and causes redundant power consumption in the divide-by-2 mode operation.

To overcome this problem, another divide-by-2/3 counter design presented in [8] is shown in Fig. 1(b). By pushing the divide control logic from the output of FF1 to its input, the output of the first stage in FF1 is

frozen when $\overline{DC} = 0$. This refrains the following stages from any switching activities for the purpose of power saving. The first stage itself, however, encounters larger power consumption than its counterpart in design [7]. This is because the pull up path is turned on all the time and the short circuit current is drawn repetitively whenever the clock signal turns “1”. The critical path delay, formed by the two FFs and the control logic, is the dominant factor of the prescaler’s maximum operating frequency. In spite of the circuit simplicity in designs [7] and [8], the inverter between FF1 and FF2, which is essential to the logic of divide-by-3, causes extra delay. Merging control logic with FF designs also introduces parallel connected transistors leading to larger parasitic capacitance adverse to both speed and power consumption. In view of these issues, our approach is keeping the circuit simplicity so that the delay and the power consumption problems can be improved at a time.

III. PROPOSED DIVIDE-BY-2/3 COUNTER DESIGN

The logic structure of the proposed design is shown in Fig. 2. The two FFs and the AND gate are common in previous designs. The OR gate for the divide control is replaced with a switch. Note that there is a negation bubble at one of the AND gate’s input. The \overline{Q} output of FF1 is thus complemented before being fed to FF2. When the switch is open, the input from FF1 is disconnected and FF2 alone divides the clock frequency by 2. When the switch is close, similar to the design in [7], FF1

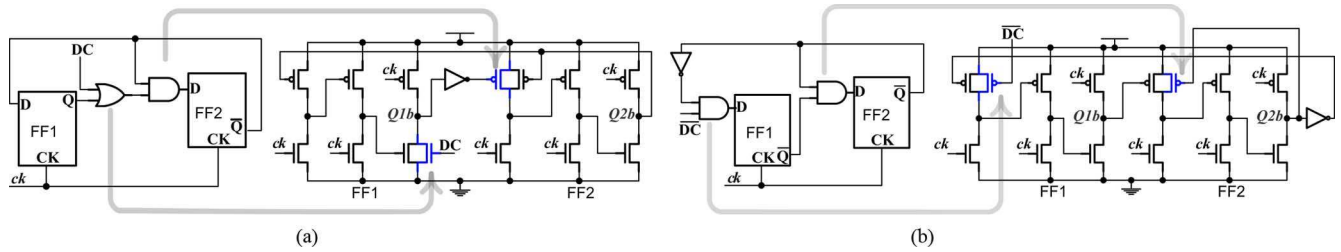


Fig. 1. Previous E-TSPC-based divide-by-2/3 counter designs. (a) Design [7]. (b) Design [8].

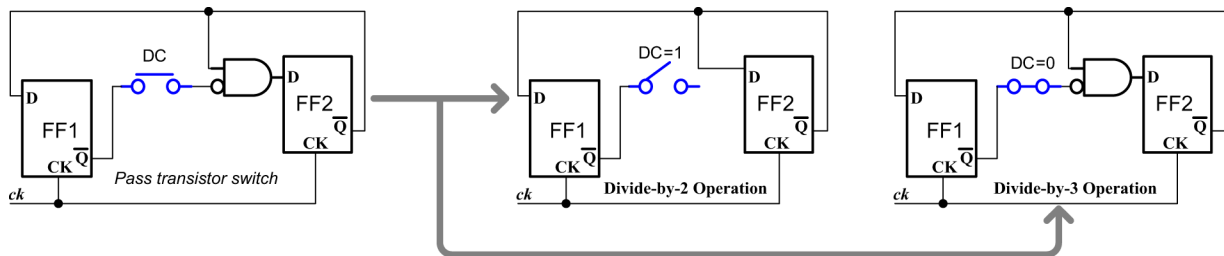


Fig. 2. Logic structure of proposed divide-by-2/3 counter design.

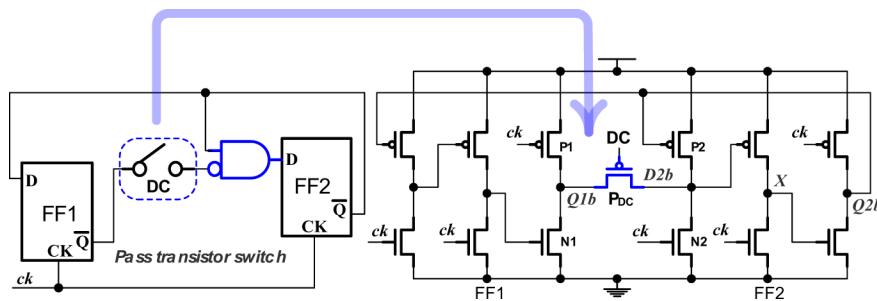


Fig. 3. MOS schematic of proposed E-TSPC-based divide-by-2/3 counter design with pass transistor logic circuit technique.

and FF2 are linked to form a counter with three distinct states. Fig. 3 shows the circuit implementation. According to the simulation results given in [12], E-TSPC design shows the best speed performance in various counter designs including the one using conventional transmission gate FFs. Besides the speed advantage, E-TSPC FFs are particularly useful for low voltage operations because of the minimum height in transistor stacking. Other than the two E-TSPC FFs, only one pMOS transistor (P_{DC}) is needed. The pMOS transistor controlled by the divide control signal serves as the switch. The AND gate plus its input inverter are achieved by way of wired-AND logic using no extra transistors at all. The proposed design scheme is far more sophisticated than the measure of simply adding one pass transistor may suggest. First of all, unlike any previous designs, the E-TSPC FF design remains in tact without any logic embedding. Both speed and power behaviors are not affected, which indicates a performance edge over the logic embedded FF design. Secondly, the inverter to complement the one of the two E-TSPC FF outputs for divide-

Divide-by-3 operations is removed in the proposed design. The circuit simplification, again, suggests the improvements in both speed and power performances. The working principle of the proposed design is elaborated as follows. When DC is “1”, the pMOS transistor P_{DC} is turned off as a switch should behave. A single pMOS transistor, however, presents a smaller capacitive load to FF1 than an inverter does in design [7]. When DC is “0”, the output of FF1, Q1b, is tied with the output node of the 1st stage inverter of FF2 through the pMOS transistor. In an E-TSPC FF design, the output of the first stage inverter can be regarded complementary to the input D i.e., \bar{D} . Therefore, a wired-OR logic is in fact implemented. Either Q2b being “0” or Q1b being “1” pulls the output node of the inverter high. This means $D2b = Q1b + Q2b$. By applying Demorgan’s law to the Boolean equation gives rise to $\overline{D2b} = \bar{D}2b = \bar{Q1b}$. Q2b which is exactly the desired logic. Since Q1b is applied to the input of the inverter needed to complement Q1b the signal can be eliminated. Before elaborating on the functional correctness of this wired OR logic, the working principle of the E-TSPC FF design is briefly reviewed. An E-TSPC FF consists of two pseudo pMOS inverters followed by a D-latch. When clock signal equals to 1, the outputs of the two inverters are pre-discharged to zero. In the mean time, the pMOS and nMOS transistors of the D-latch (the third inverter) are both turned off so that the output value holds via the parasitic capacitance. When clock signal ck turns to 0, the first two inverters enter the evaluation phase and the D-latch becomes a pseudo nMOS inverter to admit the evaluation result from the preceding inverter. Table I shows the state transition table and the excitation logic of (Q1b, Q2b) when working in the divide-by-3 mode. The wired-OR function is implemented by connecting the output node of FF1(Q1b) and the output node of the 1st stage inverter in FF2 through a pMOS transistor. Any signal inconsistency between these two nodes must be resolved by way of logic OR. In other words, signal “1” must override signal “0”. In Table I, there exist two cases of such signal inconsistency. Case 1 occurs when both Q1b and Q2b are equal to “1”. When ck=1, node D2b is both driven low by a pull down nMOS transistor N2 and pulled high by Q1b through pMOS transistor P_{DC} . Note that Q1b is actually a weak “1” retaining its level via parasitic capacitance.

TABLE
STATE TRANSITION DIVIDE-BY-3
OPERATIONS.

Current state ($Q1b, Q2b$)	Input Signal			Next state ($Q1b_n, Q2b_n$)
	$D1=Q2b$	$D2 = \overline{Q1b} \cdot Q2b$	$D2b = Q1b + \overline{Q2b}$	
11	1	0	$1=1+0^{\S}$	01
01	1	1	$0=0+0$	00
00	0	0	$1=0+1$	11
10^{\ddagger}	0	0	$1=1+1^{\S}$	11

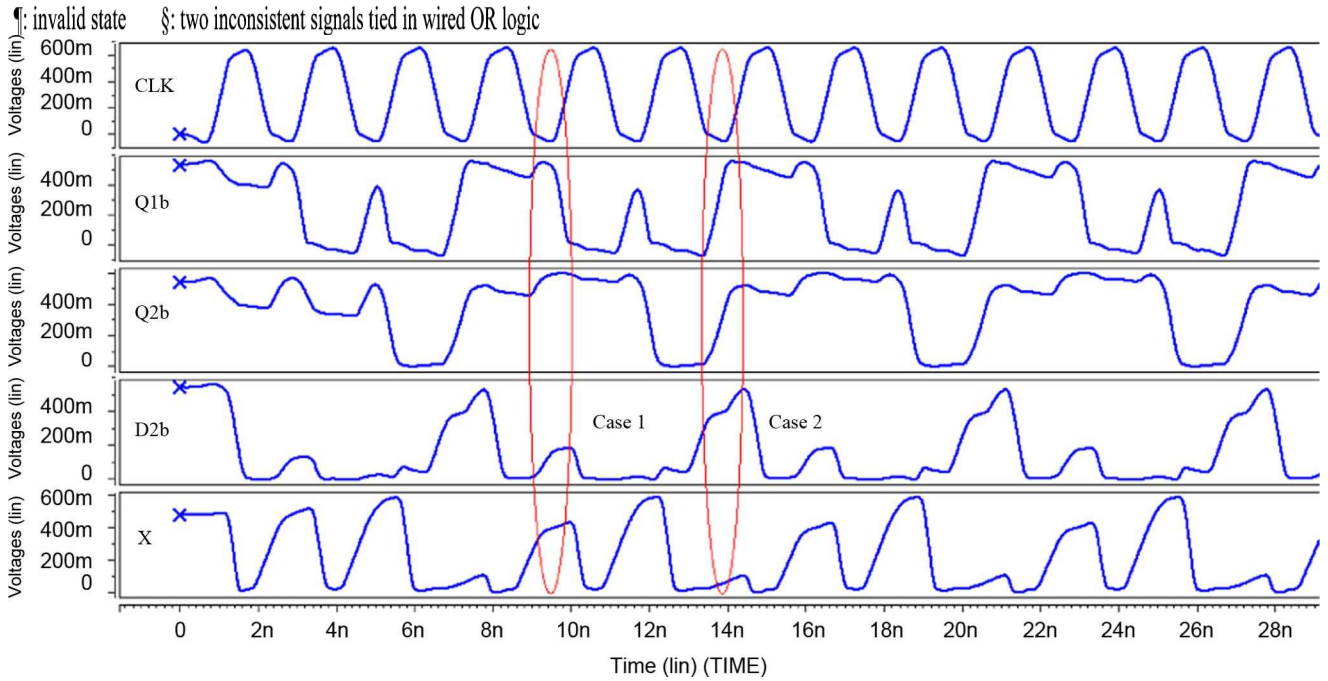


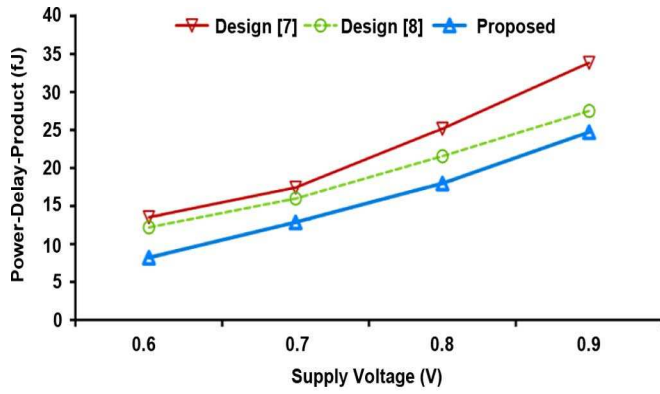
Fig. 4. Simulation waveforms for wired OR logic in divide-by-3 operations.

Although signal “0” seems to override signal “1”, this will not affect the correct value, i.e., “1”, to be latched in the evaluation phase. First, even though Q1b is vulnerable to the discharge by transistor N2, the discharge hazard is alleviated by the threshold voltage drop across pMOS transistor P_{DC} . In particular, for low V_{DD} operations, the threshold voltage, enlarged further by the body effect, can well exceed one half of the V_{DD} . This can be shown in Fig. 4 that the level degradation Q1b of is mild. Second, when the FF enters the evaluation phase, the pull down transistor N2 is cut off while transistor P1 is turned on and charges D2b through transistor P_{DC} . Refer to the D2b waveform shown in Fig. 4, the voltage level is raised up to 210 mV only. Although enlarging transistor P1 can boost the level of D2b, it will degrade the speed performance as well due to a larger capacitive load. Via proper transistor size tweaking in the following stages, this level is good enough for a correct “1” to be latched at Q1b when ck turns “1” again. A close exam at the waveform of node reveals that, in spite of a signal level over one half of the V_{DD} , it is not high enough to drive the output node to an erroneous state “0”. The second case of signal inconsistency occurs when both Q1b and are equal to “0”. In the hold phase (when $ck=1$), node is always pulled low by transistor N2. In the evaluation phase, transistor N2 is turned off and node D2b is pulled high via transistor P2. Although node keeps a contradictory signal “0”, it is actually a weak “0” and will not affect the rising of node D2b. In particular, transistor P2 charges Q1b through transistor P_{DC} as well, which coincides with the next state of Q1b. In Fig. 4, we can see a steep 0 to 1 transition of Q1b due to this effect. This enhances the prescaler’s working frequency. Also indicated in Fig. 4 are the widths of the transistors. A minimum channel length, which is 0.18 μm , is adopted in all transistor designs. Although deliberate transistor sizing is required to ensure the functionalities of wired-OR and E-TSPC, both FFs share identical sizes to reduce the design complexity.

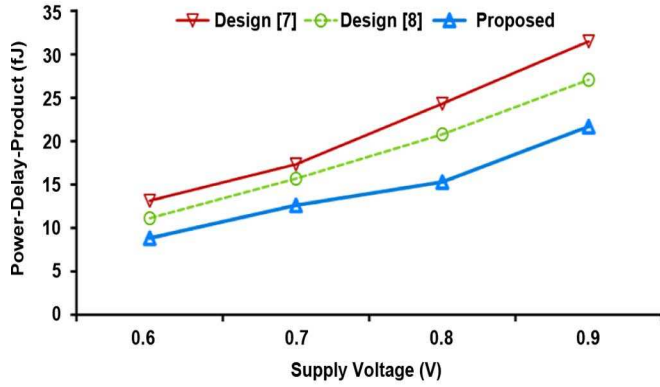
IV. SIMULATION RESULTS AND PERFORMANCE COMPARISONS

Post-layout simulations in HSPICE are conducted to compare the performances between the proposed design and the two divide-by-2/3 counter designs shown in Fig. 1, which are considered two of the best prior arts. Since the same type of E-TSPC FF is used in all three designs, any performance discrepancy would come from the logic structure. However, designs in [10] and [11] are excluded as their stacked logic structures significantly degrade their speed performance when working in the territory of low V_{DD} . The target technology is TSMC 0.18 μm 1P/6M CMOS process. Transistor sizing is subject to the optimization of power-delay-product and the capability of functioning properly at 0.6 V V_{DD} . A typical-size inverter, i.e., $1.5\mu/0.5\mu$ is used as the output load of node Q2b. Designs [7] and [8] are remapped to the same process technology and optimized using the same criteria. Refer to the transistor sizes shown in Fig. 3, the two E-TSPC FFs are identical to reduce the efforts of size tweaking. The two pseudo pMOS inverters in the E-TSPC FF design are sized to sure a logic “0” can be recognized when both pull-up and pull-down transistors are turned on. However, the size of the pull-down transistor N2 is deliberately set smaller to reduce the adverse feedback effect to the stored charge in the first FF. The pull up transistor P2 at the first stage of FF2 is also in Section III. The third (or output) stage in an E-TSPC FF is actually a latch and equal sized P- and N-type MOS transistors are employed. The setup time, hold time, D-to-Q and C-to-Q delays of our E-TSPC FF are -49.7, 792.6, 801.3, and 925.6 ps, respectively. The sizing of the pass

transistor P_{DC} is not as critical as its pivot location suggests. The layout of the proposed prescaler design is shown in Fig. 5. Table II summarizes the design features of these divide-by-2/3 counter designs at 0.6 V supply voltage. The two numbers separated by a slash in the “transistor count” indicate the number of transistors needed for the entire circuit versus that needed for the extra logic gates. The layout area of the proposed design is 21.3% and 28.6% smaller compared to design [7] and design [8], respectively. The maximum operation speed is 16.4% and 11.7% faster in divide-by-3 operations. The numbers are 11.8% and 13% in divide-by-2 operations. It is noted that, in spite of operating at a higher frequency, the proposed design consumes even less power than the other two designs. Due to the circuit simplicity, the frequency jitter of the proposed design is also smaller than the other two designs. Although the numbers compiled in Table II is under the condition of $V_{DD} = 0.6$ V, the proposed design exhibits a consistent advantages in speed and power through out other voltage settings. Since we focus on low V_{DD} operations, the voltage range of simulations is between 0.6 and 0.9 V in contrast to the nominal 1.8 V used in 0.18- m technology. Table III show the results of maximum working frequency versus supply voltage. The speed advantage of the proposed design is maintained in all voltage settings. The clock rate can be up to 2.98 GHz when V_{DD} reaches 0.9 V. Fig. 6 shows the simulation results of power-delay-product (PDP), a compound performance of power and speed, versus supply voltage. The PDP value is measured at the point of the maximum working frequency for each voltage setting and can be regarded as normalized power consumption or the energy consumption per clock cycle. The PDP curves of the proposed design are well below those of the other two designs in both operation modes. Compared to design [7], the maximum PDP saving is up to 39%. The PDP values for V_{DD} equal to 0.6 V are also listed in Table II. Fig. 7 shows the PDP performance of these designs at different process and temperature corners. The voltage is fixed at the lowest V_{DD} 0.6 V and the temperature varies from 0 C (FF corner), 25 C (SF,FS,TT corners) to 100 C (SS corner). The simulation is to show the design robustness against PT variations. The performance edge of the proposed design is maintained in all corners. Besides corner simulations, Monte Carlo simulations were also conducted and the proposed design does not exhibit any significant performance variations when compared with the other two designs. Due to space limitation, the simulation plot is not shown in this paper. Fig. 8

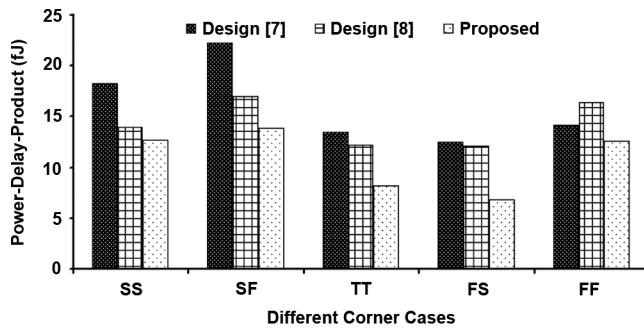


(a)

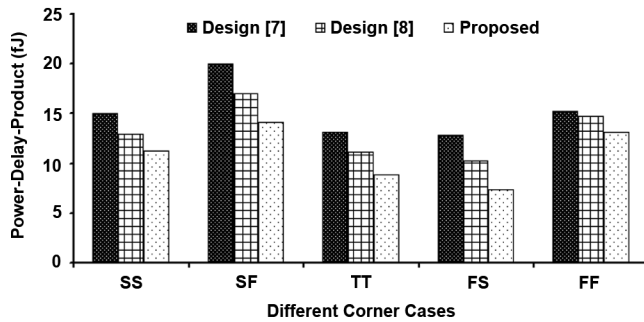


(b)

Fig. 6. Power-delay-product performances versus supply voltage. (a) Divide-by-2. (b) Divide-by-3.



(a)



(b)

Fig. 7. Comparison of power-delay-product values in different process corners. (a) Divide-by-2. (b) Divide-by-3.

by-2. (b) Divide-by-3.

depicts the post-layout simulation waveforms of the proposed design for 0.6V V_{DD} operations. The waveforms are taken at node Q2b loaded with a typical size inverter. The waveforms show an intact signal “0”

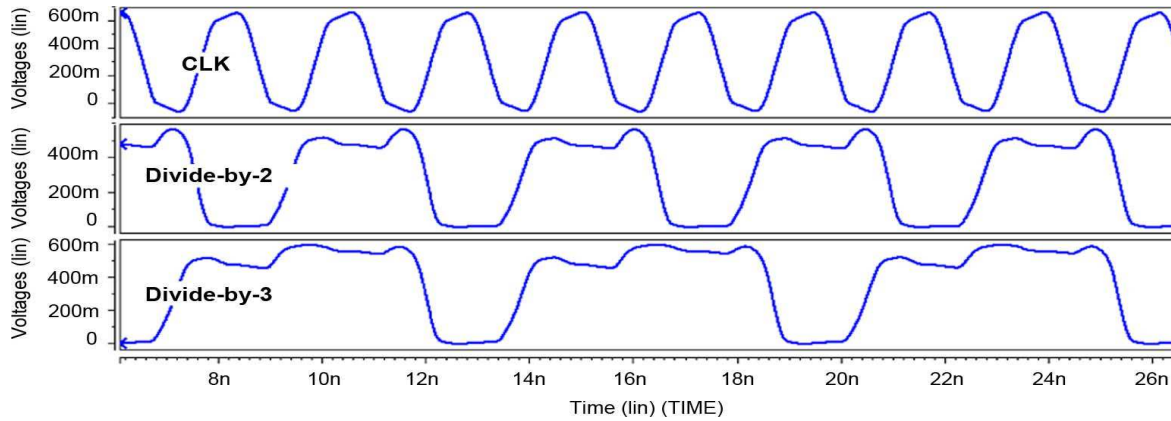


Fig. 8. Simulation waveforms of the proposed design.

TABLE II
FEATURE COMPARISON OF VARIOUS DIVIDE-BY-2/3 COUNTER DESIGNS

2/3 Counter	Design [7]	Design [8]	Proposed
# of Transistor-Count	16 / 4	16 / 4	13 / 1
Layout Area (μm^2)	91.51	100.85	71.98
Max. Freq. (MHz) $\div 2 / \div 3$	475 / 451	470 / 470	531 / 525
Average Power (μW)	6.38 / 5.92	5.74 / 5.24	4.35 / 4.61
Power-Delay-Product (fJ)	13.43 / 13.13	12.21 / 11.15	8.19 / 8.78
Jitter (ps)	13.7	10.01	7.02

TABLE III
MAXIMUM OPERATING FREQUENCY VERSUS SUPPLY VOLTAGE (GHZ)

Counter designs	0.6V	0.7V	0.8V	0.9V
Design [7]	0.45	1.14	1.93	2.73
Design [8]	0.47	1.17	1.98	2.79
Proposed	0.52	1.24	2.10	2.98

and the minimum level of signal “1” is 0.46 V, which is large enough to turn off the pull up pMOS transistor in an E-TSPC FF.

V. CONCLUSION AND DISCUSSION

In conclusion, a novel low voltage, low power divide-by-2/3 counter design suitable for high speed DLL applications is presented. The proposed design successfully simplifies the control logic and one pMOS transistor alone serves the purposes of both mode select and counter excitation logic. The circuit simplicity leads to a shorter critical path and reduced power consumption. Post layout simulation results proved its advantages in power, speed, and layout area against previous designs.

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